

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

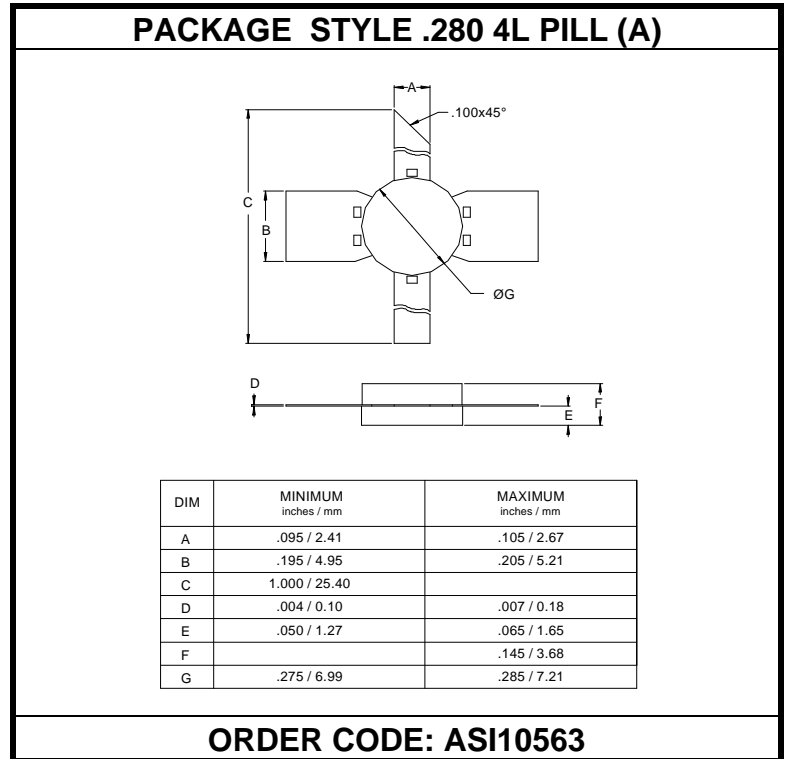
The **ASI AVD090P** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	6.5 A PEAK
<b>V<sub>CB</sub></b>	55 V
<b>P<sub>DISS</sub></b>	250 W PEAK
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	0.6 °C/W


**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	$I_C = 10\text{ mA}$	65			<b>V</b>
<b>BV<sub>CER</sub></b>	$I_C = 10\text{ mA}$ $R_{BE} = 10\ \Omega$	65			<b>V</b>
<b>BV<sub>EBO</sub></b>	$I_E = 1\text{ mA}$	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	$V_{CB} = 50\text{ V}$			6.25	<b>mA</b>
<b>h<sub>FE</sub></b>	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	10		100	<b>---</b>
<b>P<sub>G</sub></b>	$V_{CC} = 50\text{ V}$ $P_{OUT} = 90\text{ W}$ $f = 1025 - 1150\text{ MHz}$	8.5			<b>dB</b>
<b>η<sub>C</sub></b>		35			<b>%</b>